

Toshiba Infrastructure Systems & Solutions Corporation Komukai Complex

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To Whom It May Concern:

RoHS Certificate of Compliance

We certify that our microwave semiconductor products indicated below are in compliance with EU Directive 2011/65/EU and amendment 2015/863/EU on the Restriction of Hazardous Substances (RoHS).

1. Applicable Product Type

Toshiba Product Type	Description	
TGI series	Internally Matched Power GaN HEMTs	
TGM series	Power GaN Amplifier	
TIM series	Internally Matched Power GaAs FETs	
TMD series	GaAs MMICs	
TPM series	Partially Matched Power GaAs FETs	

2. Substances and the maximum allowable concentration (Threshold level)

Substance	Threshold level	Contained level
1) Cadmium and its compound	< 100 ppm	□Exceed ☑Below
2) Lead and its compound	< 1000 ppm	□Exceed ☑Below
3) Hexavalent chromium and its compound	< 1000 ppm	□Exceed ☑Below
4) Mercury and its compound	< 1000 ppm	□Exceed ☑Below
5) Polybrominated biphenyls (PBBs)	< 1000 ppm	□Exceed ☑Below
6) Polybrominated diphenyl ethers (PBDEs)	< 1000 ppm	□Exceed ☑Below
7) Bis(2-ethylhexyl) phthalate (DEHP)	< 1000 ppm	□Exceed . ☑Below
8) Butyl benzyl phthalate (BBP)	< 1000 ppm	□Exceed ☑Below
9) Dibutyl phthalate (DBP)	< 1000 ppm	□Exceed ☑Below
10) Diisobutyl phthalate (DIBP)	< 1000 ppm	□Exceed ☑Below

Signature:

Tatsuya Tokunaga

Quality Management Group Manger

Quality Assurance Department

Komukai Complex